L Number	Hits	Search Text	DB	Time stamp
1	1	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 14:30
*	_	adj protection) and (anti adj punch adj	US-PGPUB;	2000,00,00
		through adj structures)	EPO; JPO;	
		,	DERWENT;	
			IBM TDB	1
2	3	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 14:23
		adj protection) and (anti adj punch adj	US-PGPUB;	
		through)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/01 14 04
3	167	anti adj punch adj through	USPAT;	2003/08/21 14:24
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
4	2	anti adj punch adj through adj structure	USPAT;	2003/08/21 14:24
4		anci adj punch adj chrough adj scructure	US-PGPUB;	2003,00721 14.21
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
5	14	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 15:14
		adj protection) and (internal adj mos)	US-PGPUB;	
		_	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	1	6008080.pn. and pocket	USPAT;	2003/08/21 15:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
7	2	6100141 nn and internal	USPAT;	2003/08/21 15:52
'		6100141.pn. and internal	US-PGPUB;	2003/08/21 13:32
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 09:40
		adj protection) and (active adj region)	US-PGPUB;	
		and (breakdown adj enhanced adj layer)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	387		USPAT;	2003/08/20 17:22
		adj protection) and (active adj region)	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	1	((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:23
		adj protection) and (reduce adj breakdown	US-PGPUB;	2303,03,20 17.23
		adj voltage adj across adj doped adj	EPO; JPO;	
		drain)	DERWENT;	
			IBM_TDB	
-	1	((esd or (electrostatic adj discharge))	USPĀT;	2003/08/20 17:24
		adj protection) and (reduce adj breakdown	US-PGPUB;	a
		adj voltage adj across adj drain)	EPO; JPO;	1
			DERWENT;	1
	4.3	(/ord or /olostwortstip add discharge))	IBM_TDB	2003/08/20 17:32
-	41	((esd or (electrostatic adj discharge))	USPAT; US-PGPUB;	2003/00/20 11:32
		adj protection) and (reduce adj breakdown adj voltage)	EPO; JPO;	
		auj voicage,	DERWENT;	
			IBM TDB	
_	0	((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:36
1		adj protection) and (first adj gate adj	US-PGPUB;	
		oxide adj thickness)	EPO; JPO;	
		_	DERWENT;	
			IBM_TDB	
-	70	((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:41
		adj protection) and (thick adj gate adj	US-PGPUB;	
		oxide)	EPO; JPO;	
			DERWENT; IBM TDB	
L			TDM IND	<u></u>

		((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:42
_		, , ,	US-PGPUB:	2003/00/20 17.42
		adj protection) and (multiple adj gate adj	EPO; JPO;	
		oxide adj thickness)	DERWENT;	
			IBM TDB	
				2002/00/20 17-42
-	0	, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	USPAT;	2003/08/20 17:42
į		adj protection) and (multiple adj gate adj	US-PGPUB;	
		oxide)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 08:43
		adj protection) and (different adj gate	US-PGPUB;	
		adj oxide)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	5861345.pn. and (aspect adj ratio)	USPAT;	2003/08/21 08:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	5656337.pn. and (aspect adj ratio)	USPAT;	2003/08/21 08:44
		and (appear any radio)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	6	((esd or (electrostatic adj discharge))	USPAT:	2003/08/21 14:20
-		adj protection) and (pocket adj	US-PGPUB;	2003,00,21 14.20
		adj protection; and (pocket adj implantations)	EPO; JPO;	
		Implantations;	DERWENT;	
			IBM TDB	
1	1		TRM TAR	1